

1-4. (Cancelled)

5. (Previously Presented) A single crystal semiconductor structure comprising:

a trench formed in a single crystal semiconductor body surface, said trench having upper sidewall portions perpendicular to and extending from said semiconductor body surface, said perpendicular sidewalls of the upper portion of the trench disposed in different crystallographic planes of the body;

a first one of said sidewall portions of said trench disposed in a first one of the different crystallographic planes, said first crystallographic plane perpendicular to said surface;

a first layer of silicon dioxide material grown on said first sidewall portions at a first rate and to a first thickness when subjected to a thermal oxidation process;

a second one of said sidewall portions of said trench disposed in a second one of the different crystallographic planes, said second crystallographic plane also perpendicular to said surface; and

a second layer of silicon dioxide grown on both said second sidewall portion at a second rate, and on said first layer of said silicon dioxide material at a rate slower than said second rate such that the thickness of said second layer of silicon dioxide on said second sidewall portions is substantially equal to the thickness of both said first and second layers of silicon dioxide on said first sidewall portions.

6. (Previously Presented) A single crystal semiconductor structure comprising:

a trench formed in a single crystal semiconductor body surface having upper sidewall portions perpendicular to and extending from said semiconductor body surface,

said perpendicular sidewalls of the upper portion of the trench disposed in different crystallographic planes of said semiconductor body;

a relatively thin material formed on selected sidewall portions of said trench residing in a first one of said different crystallographic planes perpendicular to said surface;

a layer of silicon dioxide grown over said relatively thin material at a first rate by a thermal oxidation process to a selected thickness; and

said silicon dioxide grown at a second rate during said thermal oxidation process on unselected sidewall surface portions of said trench without said thin material, said unselected sidewalls residing in a second one of said different crystallographic planes that is also perpendicular to said surface, said second rate faster than said first rate such that the resulting thickness of said silicon dioxide grown over both the selected sidewall portions and the unselected sidewall portions is substantially uniform.

7. (Previously Presented) The semiconductor body of claim 5 wherein said first sidewall portions are disposed in the <110> crystallographic plane and said second sidewall portions are disposed in the <100> crystallographic plane.

8. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material is silicon nitride.

9. (Previously Presented) The semiconductor body of claim 6 further comprising another layer of silicon dioxide formed on said relatively thin material such that said another layer of silicon dioxide and said layer of silicon dioxide grown over said

relatively thin material have a combined thickness substantially the same as the thickness of said layer of silicon dioxide grown on said unselected surface portions of said semiconductor body.

10. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material is less than approximately 20 Angstroms.

11. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material forms a layer which is thinner than the corresponding oxide layer grown on the selected and unselected surface portions.

12. (Previously Presented) The semiconductor body of claim 6 wherein said first sidewall portions are disposed in the <110> crystallographic plane and said second sidewall portions are disposed in the <100> crystallographic plane.

13. (Previously Presented) The semiconductor body of claim 1 wherein said trench is oval shaped.

14. (Previously Presented) The semiconductor body of claim 5 wherein said trench is oval shaped.

15. (Previously Presented) The semiconductor body of claim 6 wherein said trench is oval shaped.

16. (Previously Presented) The semiconductor body of claim 1 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.
17. (Previously Presented) The semiconductor body of claim 5 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.
18. (Previously Presented) The semiconductor body of claim 6 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.